



DMT6030LFCL

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
	25mΩ @ V _{GS} = 10V	6.5A
60V	$34m\Omega @ V_{GS} = 4.5V$	5.2A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Power Management Functions**
- Load Switch

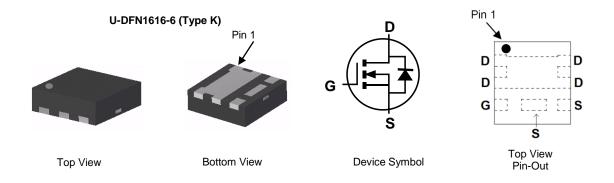
60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 0.6mm Profile—Ideal for Low Profile Applications
- Low On-Resistance
- PCB Footprint of 2.56mm²
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: U-DFN1616-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Lead Free Plating (NiPdAu Finish over Copper Leadframe). Solderable per MIL-STD-202, Method 208 @
- Weight: 0.003 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6030LFCL-7	U-DFN1616-6 (Type K)	3,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes: 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds. 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1:

U-DFN1616-6 (Type K)



63L = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Date Code Key												
Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	E		Н		J	K	L	М	Ν	0	Р	R
												_
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2:

U-DFN1616-6 (Type K)

	63L
	YWX
•	

63L = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date	Code	Kev
Daie	COUC	1100

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7		0	1	2	3	4	5	6	7	8	9
					1							
Week	1-26			27-52				53				
Code		А	A-Z			a-z			Z			
Internal Code	Su	ın	Mor	n	Tue	1	Ned	Thu		Fri		Sat
Code	Т	-	U		V		W	Х		Y		Ζ



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	Vdss	60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C T _A = +70°C	lo	6.5 5.2	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			ldм	30	A
Maximum Body Diode Continuous Current (Note 6)	ls	1.7	А		
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle :	= 1%)		Ism	30	А

Thermal Characteristics

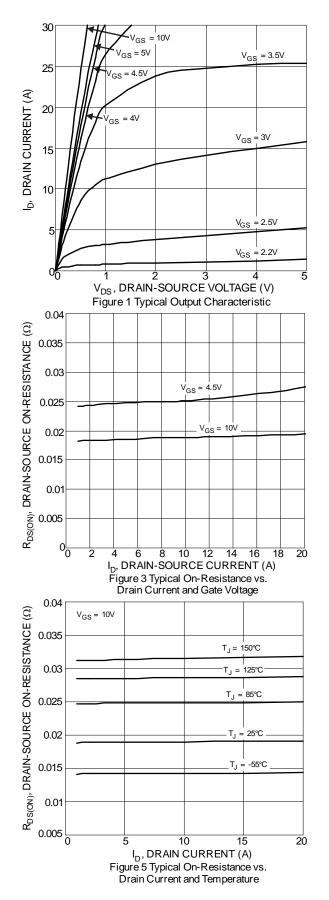
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	160	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.58	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	79	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	16.7	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

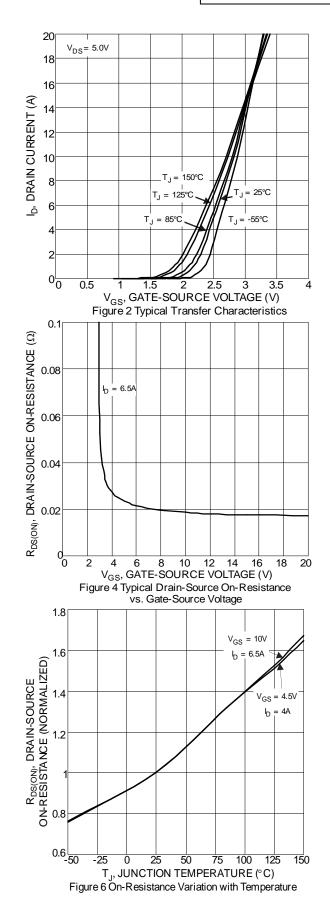
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	•					
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	Vgs = 0V, ID = 250µA
Zero Gate Voltage Drain Current	IDSS		_	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(TH)	1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Proven	—	19	25	mΩ	Vgs = 10V, ID = 6.5A
	R _{DS(ON)}	_	25	34	11122	$V_{GS} = 4.5V, I_{D} = 4A$
Diode Forward Voltage	Vsd	—	0.7	1.2	V	$V_{GS} = 0V$, $I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		639	—		
Output Capacitance	Coss		166	—	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1MHz
Reverse Transfer Capacitance	Crss	_	13.1	—		
Gate Resistance	Rg	—	1.4	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	9.1	_		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.5	_	nC	$V_{DS} = 30V. I_{D} = 10A$
Gate-Source Charge	Qgs	—	1.2	—	nc	VDS = 30V, ID = 10A
Gate-Drain Charge	Q _{gd}	_	2.0	_		
Turn-On Delay Time	td(on)	_	2.6	_		
Turn-On Rise Time	t _R		2.2	_		$V_{GS} = 10V, V_{DD} = 30V,$
Turn-Off Delay Time	tD(OFF)		10.7		ns	$R_g = 6\Omega$, $I_D = 10A$
Turn-Off Fall Time	tF	_	3.4]	
Body Diode Reverse Recovery Time	trr	_	26.5		ns	
Body Diode Reverse Recovery Charge	Qrr		12.3		nC	$I_F = 10A, dI/dt = 100A/\mu s$

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:

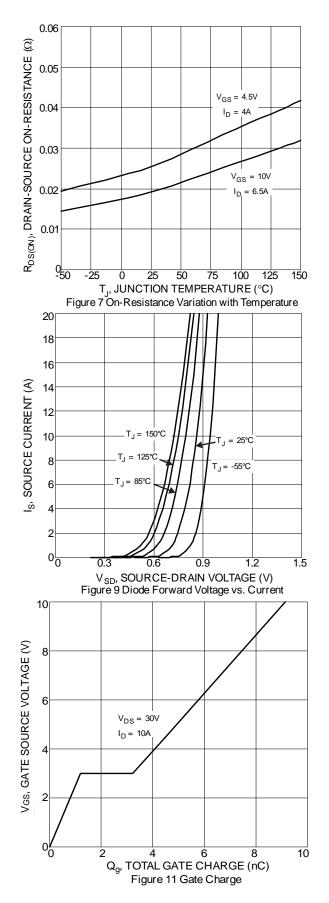


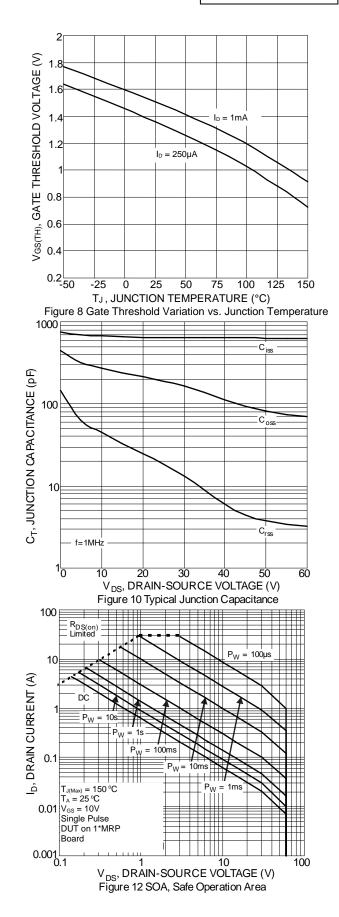




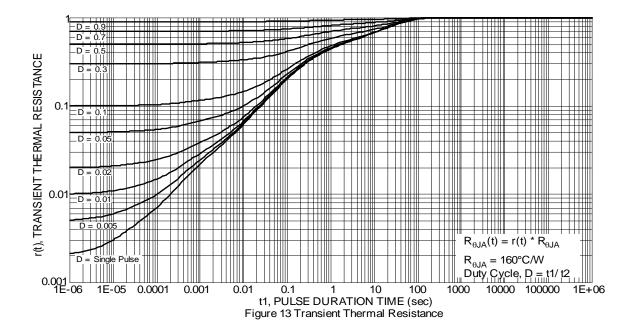
DMT6030LFCL Document number: DS40421 Rev. 4 - 2







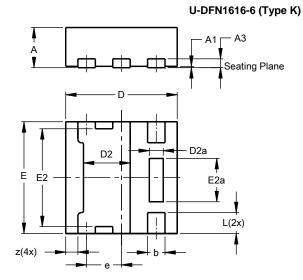






Package Outline Dimensions

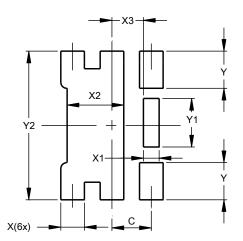
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN1616-6								
(Туре К)								
Dim	Min	Max	Тур					
Α	0.55	0.60	0.575					
A1	0.00	0.05	0.02					
A3	-	_	0.13					
b	0.20	0.30	0.25					
D	1.55	1.65	1.60					
D2	0.57	0.77	0.67					
D2a	0.10	0.30	0.20					
е	-	_	0.50					
Е	1.55	1.65	1.60					
E2	1.30	1.50	1.40					
E2a	0.52	0.72	0.62					
L	0.25	0.35	0.30					
z	-	_	0.175					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.500
Х	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900

U-DFN1616-6 (Type K)



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